Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT82 (SIP3) plastic package intended for use in general purpose bidirectional switching and phase control applications.

2. Features and benefits

- · High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- · Less sensitive gate for improved noise immunity
- Triggering in all four quadrants
- · Compact package

3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute	maximum rating					
V_{DRM}	repetitive peak off-state voltage	600				V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; Fig. 1; Fig. 2; Fig. 3	4		А	
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	25		А	
Symbol	Parameter	Conditions Min Typ Max		Max	Unit	
Static ch	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	11	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	30	70	mA

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	[]	
2	T2	main terminal 2		Ζ
3	G	gate	[[T2 T1
mb	T2	mounting base; main terminal 2		sym051

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BT134-600	SIP3	plastic single-ended package; 3 leads (in-line)	SOT82			

7. Marking

Table 4. Marking codes

Type number	Marking codes
BT134-600	BT134-600

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 107 \text{ °C}$; Fig 1; Fig 2; Fig 3	4	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig 4; Fig 5	25	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	27	Α
l ² t	I ² t for fusing	t _P = 10 ms; SIN	3.1	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 70 mA	50	A/µs
		I _G = 70 mA	50	A/µs
		I _G = 70 mA	50	A/µs
		I _G = 140 mA	10	A/µs
I _{GM}	peak gate current		2	А
P_{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		125	°C

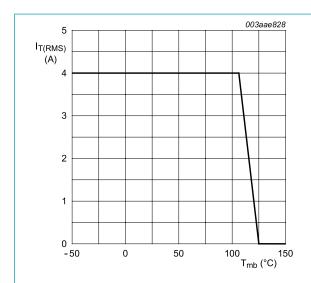
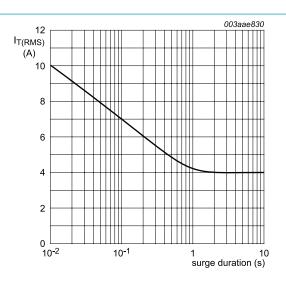


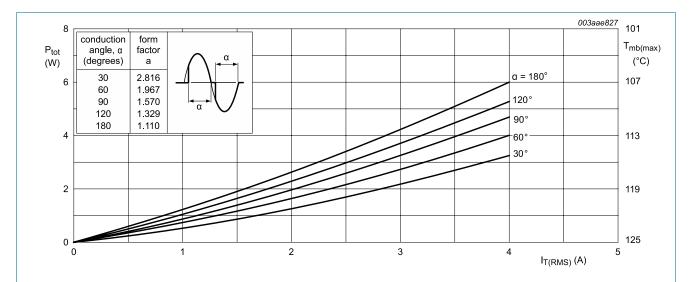
Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} \le 107 \text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

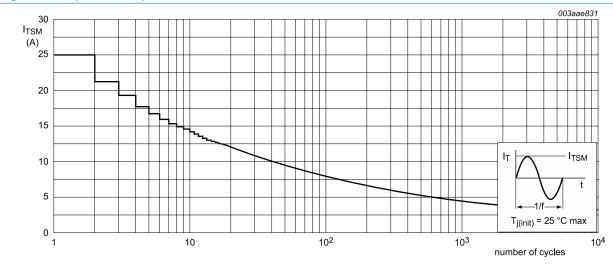
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 α = conduction angle

a = form factor = $I_{T(RMS)} / I_{T(AV)}$

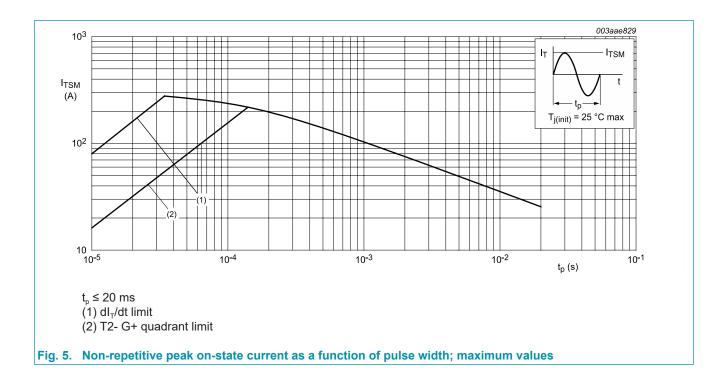
Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance	half cycle; Fig 6	-	-	3.7	K/W
from junction to mounting base		half cycle; Fig 6	-	-	3	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	100	-	K/W

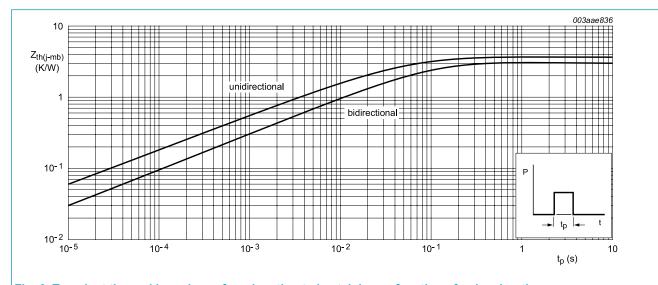


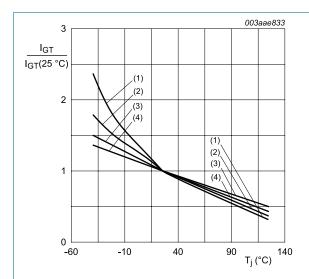
Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

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10. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	11	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	30	70	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	7	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 8$	-	16	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	5	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	7	30	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	5	15	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I_D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	100	250	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 95 ^{\circ}\text{C}; I_T = 4 \text{ A};$ $dI_{com}/dt = 1.8 \text{ A/ms}; gate open circuit}$	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	$V_D = 600 \text{ V}; I_{TM} = 6 \text{ A}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

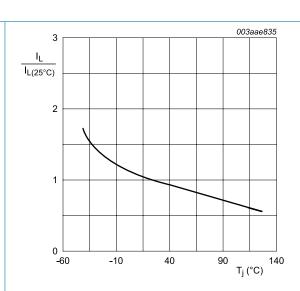


Fig. 8. Normalized latching current as a function of junction temperature

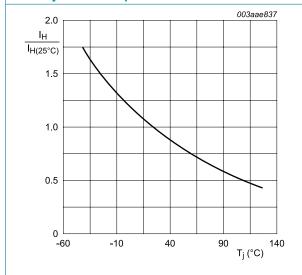
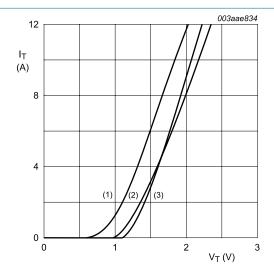


Fig. 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.27 \text{ V}; R_s = 0.091 \Omega$

(1) $T_j = 125$ °C; typical values (2) $T_j = 125$ °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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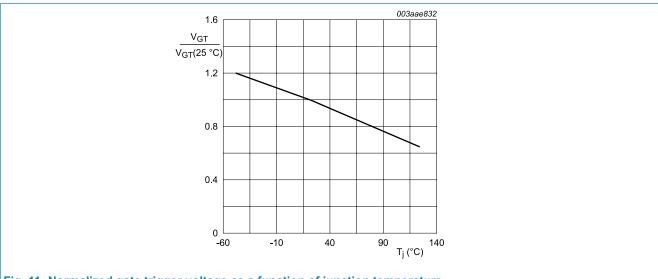
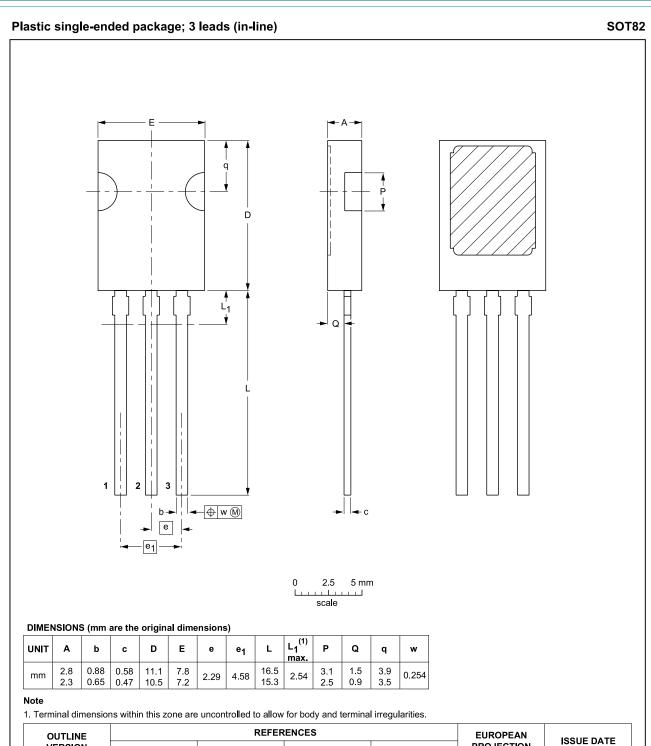


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline



OUTLINE		REFER	REFERENCES			ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT82						97-06-11	

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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For more information, please visit: http://www.ween-semi.com
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Date of release: 26 April 2018

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